

General Purpose Transistors 通用三极管

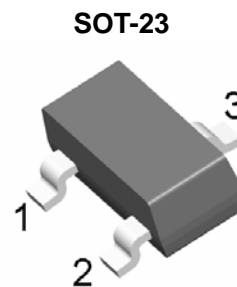
FHT1815

DESCRIPTION & FEATURES 概述及特点

Excellent h_{FE} Linearity h_{FE} 线性特性极好
 $h_{FE}(0.1mA)/h_{FE}(2mA)=0.95(Typ.)$
 High 高 h_{FE} : $h_{FE}=70\sim700$
 Low Noise 低噪声: $NF=1dB(Typ.),10dB(Max.)$
 Complementary to FHT1015 与 FH1015 互补

PIN ASSIGNMENT 引脚说明

| PIN NAME 管脚符号 | PIN NUMBER 引脚序号 | FUNCTION 功能 |
|------------------|-----------------|----------------|
| | SOT-23 | |
| B | 1 | BASE |
| E | 2 | EMITTER |
| C | 3 | COLLECTOR |



MAXIMUM RATINGS($T_a=25^\circ C$) 最大额定值

| CHARACTERISTIC 特性参数 | Symbol 符号 | Rating 额定值 | Unit 单位 |
|---------------------------------------|-----------|------------|---------|
| Collector-Emitter Voltage 集电极-发射极电压 | V_{CEO} | 50 | Vdc |
| Collector-Base Voltage 集电极-基极电压 | V_{CBO} | 60 | Vdc |
| Emitter-Base Voltage 发射极-基极电压 | V_{EBO} | 5.0 | Vdc |
| Collector Current—Continuous 集电极电流-连续 | I_C | 150 | mAdc |
| Base Current 基极电流 | I_B | 30 | mAdc |

THERMAL CHARACTERISTICS 热特性

| CHARACTERISTIC 特性参数 | Symbol 符号 | Max 最大值 | Unit 单位 |
|--|----------------|---------------|------------|
| Collector Power Dissipation 集电极耗散功率 | P_c | 300 | mW |
| Junction and Storage Temperature 结温和储存温度 | T_j, T_{stg} | 150, -55 ~150 | $^\circ C$ |

DEVICE MARKING 打标

h_{FE} (1) FHT1815=BO (70~140), FHT1815Y=BY (120~240),
 FHT1815G=BG (200~400), FHT1815L=BL (350~700)

ELECTRICAL CHARACTERISTICS 电特性

($T_A=25^\circ C$ unless otherwise noted 如无特殊说明, 温度为 $25^\circ C$)

| Characteristic 特性参数 | Symbol 符号 | Test Condition 测试条件 | Min 最小值 | Type 典型值 | Max 最大值 | Unit 单位 |
|--|---------------|----------------------------------|---------|----------|---------|---------|
| Collector Cutoff Current 集电极截止电流 | I_{CBO} | $V_{CB}=60V, I_E=0$ | — | — | 0.1 | μA |
| Emitter Cutoff Current 发射极截止电流 | I_{EBO} | $V_{EB}=5V, I_C=0$ | — | — | 0.1 | μA |
| Collector-Emitter Breakdown Voltage 集电极-发射极击穿电压 | $V_{(BR)CEO}$ | $I_C=1.0mA$ | 50 | — | — | V |
| Collector-Base Breakdown Voltage 集电极-基极击穿电压 | $V_{(BR)CBO}$ | $I_C=100\mu A$ | 60 | — | — | V |
| Emitter-Base Breakdown Voltage 发射极-基极击穿电压 | $V_{(BR)EBO}$ | $I_E=100\mu A$ | 5 | — | — | V |
| DC Current Gain 直流电流增益 | h_{FE} | $V_{CE}=6V, I_C=2mA$ | 70 | — | 700 | — |
| Collector-Emitter Saturation Voltage 集电极-发射极饱和压降 | $V_{CE(sat)}$ | $I_C=100mA, I_B=10mA$ | — | — | 0.25 | V |
| Base-Emitter Voltage 基极-发射极电压 | V_{BE} | $V_{CE}=5.0V, I_C=10mA$ | — | — | 0.82 | V |
| Transition Frequency 特征频率 | f_T | $V_{CE}=5.0V, I_C=10mA$ | 100 | 180 | — | MHz |
| Collector Output Capacitance 输出电容 | C_{ob} | $V_{CB}=10V, I_E=0,$ $f=1MHz$ | — | 4.0 | 7.0 | pF |